

MOSFET PRODUCT CATALOGUE

MOSFET 产品手册



2020年10月第三版

公司简介

扬州扬杰电子科技股份有限公司是国内少数集半导体分立器件芯片设计、制造、器件封装测试、终端销售与服务等产业链垂直



一体化 (IDM) 的杰出厂商。产品线涵盖分立器件芯片、整流器件、保护器件、小信号、MOSFET、功率模块、碳化硅等一揽子产品解决方案。

公司产品广泛应用于电源、家电、照明、安防、网通、消费电子、新能源、工控、汽车电子等多个领域。

公司于 2014 年 1 月 23 日在深交所上市，证券代码 300373，相信在您的关怀支持下，我们一定能够实现让世界信赖中国半导体的愿景。

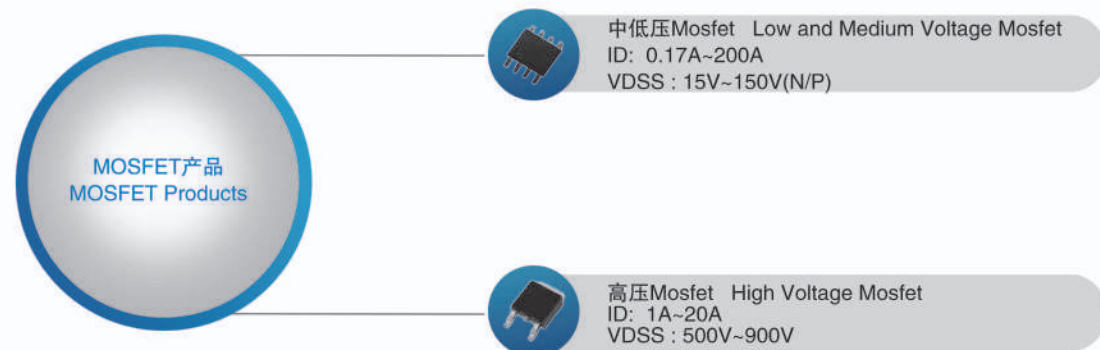
Yangzhou Yangjie Electronic Technology Co., Ltd. is one of the few outstanding IDM manufactures in China which integrates discrete semiconductor chip design and production, semiconductor component assembly and test as well as market sales&services. We have a wide range of products including discrete semiconductor chips, rectifiers, protection devices, small signal parts, mosfets, power modules and SiC diodes which offer one-stop solution to our customers.

Our products are widely used in power supply, home appliance, lighting, security, telecommunication, customer electronics, green energy, industrial and automatic control, automotive electronics and other fields.

We were listed in Shenzhen Stock Exchange Market in 23 january, 2014 with stock code 300373. We believe that we could achieve our vision "let the world trust Chinese semiconductor" with your support.



01 产品大类 Product Type



02 产品特点 Product Features

- a** ◆全系列MOSFET产品方案，多种封装外形
Complete mosfet product portfolio with diversified packages
- b** ◆中低压MOSFET 8英寸、高压MOSFET 6英寸自主晶圆设计能力
8" Low and medium voltage Mosfet and 6" high voltage Mosfet in house wafer design capability
- c** ◆中低压MOSFET沟槽和屏蔽栅工艺，高压MOSFET平面工艺
Low and medium voltage Mosfet Trench and SGT platform and high voltage Mosfet planar platform
- d** ◆超低内阻的芯片设计
Super low R_{ds(on)} chip design
- e** ◆先进的自动化生产设备确保产品精度和稳定的可靠性
Advanced automatic production ensure parameter accuracy and stable reliability

03 产品应用 Product Application



04 我们的客户 Our Client



CATALOG

目录

- 中低压MOSFET
LOW AND MEDIUM VOLTAGE MOSFET1-7
- 高压MOSFET
HIGH VOLTAGE MOSFET8
- 封装尺寸图
OUTLINE DRAWING9-11
- 焊盘尺寸图
SUGGESTED PAD LAYOUT12-15
- 包装形态
PACKING16
- 可靠性试验项目
RELIABILITY TEST ITEM17

中低压MOSFET LOW AND MEDIUM VOLTAGE MOSFET

P Channel MOS:

型号 TYPE NO.	结构 Configuration	产品 极性 N/P	漏源电压 V _{DSS} (V)	工作 电流 I _d (A)	耗散 功率 Pd	栅源 电压 V _{GS} (V)	阈值 电压 V _{TH} (V)	导通电阻R _{dson} (mΩ)		导通电阻R _{dson} (mΩ)		导通电阻R _{dson} (mΩ)		导通电阻R _{dson} (mΩ)		封装类型 Package
								@V _{GS} 10V	@V _{GS} 4.5V	@V _{GS} 2.5V	@V _{GS} 1.8V	Typ	Max	Typ	Max	
BSS84	Single	P	-60	-0.17	0.35	±20	-1.4	3300	8000	3500	9900	-	-	-	-	SOT-23
BSS84W	Single	P	-60	-0.17	0.15	±20	-1.4	3300	8000	3500	9900	-	-	-	-	SOT-323
YJL2303A	Single	P	-30	-3	1.1	±20	-1.5	56	75	79	109	-	-	-	-	SOT-23
YJL3407A	Single	P	-30	-4.1	1.2	±20	-1.5	36	49	52	65	-	-	-	-	SOT-23
YJL3401A	Single	P	-30	-4.4	1.2	±12	-0.9	40	55	47	66	60	94	-	-	SOT-23
YJL3407AL	Single	P	-30	-4.1	1.3	±20	-1.5	36	49	52	65	-	-	-	-	SOT-23-3L
YJL3401AL	Single	P	-30	-4.4	1.5	±12	-0.9	40	55	47	66	60	94	-	-	SOT-23-3L
YJL07P03AL	Single	P	-30	-7	1.9	±20	-1.5	18.5	25	24.5	36	-	-	-	-	SOT-23-3L
YJJ06P03A	Single	P	-30	-6	1.5	±20	-1.5	36	49	52	65	-	-	-	-	SOT-23-6L
YJS4953A	Dual	P	-30	-5.1	2.5	±20	-1.5	30	43	46	59	-	-	-	-	SOP-8
YJS9435A	Single	P	-30	-5.1	2.5	±20	-1.5	30	43	46	59	-	-	-	-	SOP-8
YJS4435A	Single	P	-30	-10	3	±20	-1.5	15.3	20.8	20.8	27.8	-	-	-	-	SOP-8
YJS7328A	Dual	P	-30	-10	3	±20	-1.5	18.5	23	24.5	34	-	-	-	-	SOP-8
YJS4407A	Single	P	-30	-12	3.2	±25	-1.8	9.3	12.5	13.8	20.8	-	-	-	-	SOP-8
YJS4407B	Single	P	-30	-14	3.3	±20	-1.5	8.9	11	11.5	15	-	-	-	-	SOP-8
YJS4409A	Single	P	-30	-18	3.4	±25	-1.5	5.1	6	7.5	10	-	-	-	-	SOP-8
YJS4447B	Single	P	-30	-18	3.4	±25	-1.8	5	6.2	6.9	10	-	-	-	-	SOP-8
YJQ40P03A	Single	P	-30	-40	32	±25	-1.8	9.8	15	15.5	25	-	-	-	-	DFN3333
YJQ50P03A	Single	P	-30	-50	75	±25	-1.8	5	6.2	6.9	11	-	-	-	-	DFN3333
YJG40P03A	Single	P	-30	-40	45	±25	-1.8	9	14	14.5	24	-	-	-	-	PDFN5060
YJD45P03A	Single	P	-30	-45	75	±25	-1.8	5.5	8	8	13	-	-	-	-	TO-252
YJD70P03A	Single	P	-30	-70	110	±25	-1.8	4.5	6	6.6	10	-	-	-	-	TO-252
YJL3139K	Single-ESD	P	-20	-0.65	0.35	±12	-0.61	-	-	360	520	570	750	860	1300	SOT-23
YJL2301F	Single	P	-20	-2	0.7	±10	-0.62	-	-	81	94	109	127	152	187	SOT-23
YJL2301C	Single	P	-20	-3.4	1	±10	-0.62	-	-	42	51	55	67	76	91	SOT-23
YJL2305B	Single	P	-20	-5.4	1.2	±10	-0.62	-	-	27	39	36	49	48	63	SOT-23
YJL3415A	Single-ESD	P	-20	-5.6	1.3	±12	-0.62	-	-	29	42	36	55	55	100	SOT-23
YJS2301A	Dual	P	-20	-3.7	1.2	±10	-0.62	-	-	42	51	55	67	76	91	SOT-23-6L
YJS2305A	Single	P	-20	-5.4	1.2	±10	-0.62	-	-	27	39	36	49	48	63	SOT-23-6L
YJL3139KW	Single-ESD	P	-20	-0.65	0.2	±12	-0.61	-	-	395	520	570	750	860	1300	SOT-323
YJL2101W	Single	P	-20	-2	0.25	±10	-0.62	-	-	100	130	135	170	175	250	SOT-323
YJL3139KDW	Dual-ESD	P	-20	-0.65	0.2	±12	-0.61	-	-	360	520	570	750	860	1300	SOT-363
YJL3139KT	Single-ESD	P	-20	-0.65	0.18	±12	-0.61	-	-	360	520	570	750	860	1300	SOT-723
YJS2022A	Single	P	-20	-13	3	±10	-0.62	-	-	10	17	13	20	18	26	SOP-8
YJQ03P02A	Single	P	-20	-3	1	±10	-0.62	-	-	81	94	109	127	152	187	DFN2020-6L
YJQ2301A	Dual	P	-20	-4	1.3	±10	-0.62	-	-	42	51	55	67	76	91	DFN2020-6L
YJQ3415A	Single-ESD	P	-20	-6.2	2.2	±12	-0.62	-	-	29	42	36	55	55	100	DFN2020-6L
YJQ4666B	Single	P	-20	-7	2.2	±10	-0.62	-	-	24.5	36.5	33.5	46.5	45.5	60.5	DFN2020-6L



中低压MOSFET LOW AND MEDIUM VOLTAGE MOSFET

P Channel MOS:

型号 TYPE NO.	结构 Configuration	产品 极性 N/P	漏源电压 V _{DSS} (V)	工作 电流 I _d (A)	耗散 功率 P _d	栅源 电压 V _{GS} (V)	阈值 电压 V _{TH} (V)	导通电阻R _{dson} (mΩ) @VGS10V		导通电阻R _{dson} (mΩ) @VGS4.5V		导通电阻R _{dson} (mΩ) @VGS2.5V		导通电阻R _{dson} (mΩ) @VGS1.8V		封装类型 Package
							Typ	Typ	Max	Typ	Max	Typ	Max	Typ	Max	
YJQ1216A	Single	P	-20	-16	18	±10	-0.62	-	-	11	19	14	22	20	30	DFN2020-6L
YJQD30P02A	Dual	P	-20	-30	21	±10	-0.62	-	-	11	19	14	22	20	30	DFN3333
YJQ55P02A	Single	P	-20	-55	38	±10	-0.62	-	-	6.5	8.3	8	10	10.3	15	DFN3333
YJL2301N	Single	P	-19	-1.7	0.7	±10	-0.62	-	-	94	114	130	169	189	259	SOT-23
YJL2301G	Single	P	-19	-2	0.7	±10	-0.62	-	-	65	85	92	114	130	162	SOT-23
YJL2301D	Single	P	-19	-3.8	1	±10	-0.62	-	-	36	47	48	63	67	85	SOT-23
YJL2301GW	Single	P	-19	-1.5	0.25	±10	-0.62	-	-	90	108	105	130	140	230	SOT-323
YJL2305A	Single	P	-15	-5.6	1.2	±10	-0.62	-	-	23	30	31	40	44	56	SOT-23



中低压MOSFET LOW AND MEDIUM VOLTAGE MOSFET

N Channel MOS:

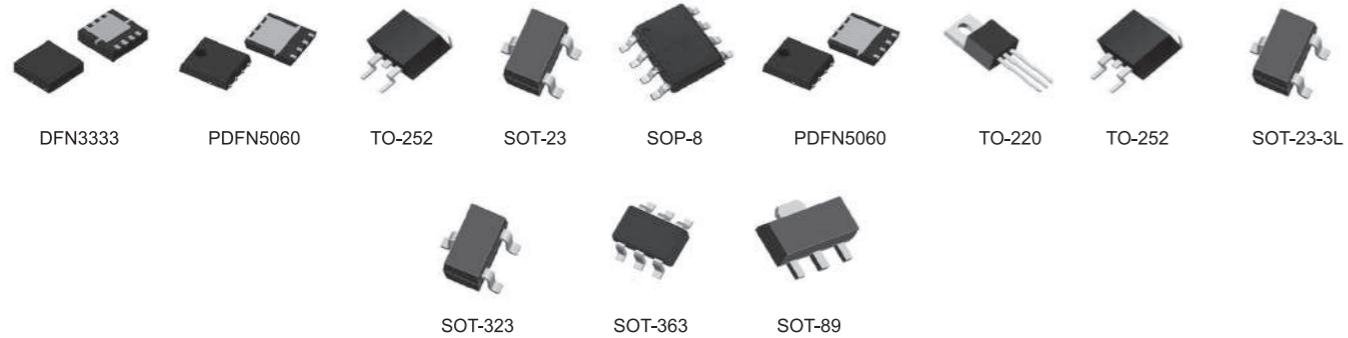
型号 TYPE NO.	结构 Configuration	产品 极性 N/P	漏源电压 V _{DSS} (V)	工作 电流 I _d (A)	耗散 功率 P _d	栅源 电压 V _{GS} (V)	阈值 电压 V _{TH} (V)	导通电阻R _{dson} (mΩ) @VGS10V		导通电阻R _{dson} (mΩ) @VGS4.5V		导通电阻R _{dson} (mΩ) @VGS2.5V		导通电阻R _{dson} (mΩ) @VGS1.8V		封装类型 Package
							Typ	Typ	Max	Typ	Max	Typ	Max	Typ	Max	
YJL3134K	Single-ESD	N	20	0.9	0.35	±12	0.75	-	-	135	260	185	360	265	570	SOT-23
YJL2302B	Single	N	20	3	0.7	±10	0.78	-	-	38.5	50	53.5	70	-	-	SOT-23
YJL2302A	Single	N	20	4.3	1	±10	0.85	-	-	21	27	28	37	-	-	SOT-23
YJL2300A	Single	N	20	4.5	1	±10	0.62	-	-	19.5	25	25	32	33	46	SOT-23
YJL2312A	Single	N	20	6.8	1.25	±10	0.62	-	-	13.5	18	17	22	22	39	SOT-23
YJL3416A	Single-ESD	N	20	7	1.3	±12	0.62	-	-	13	18	17	22	27	39	SOT-23
YJL2312AL	Single	N	20	7.6	1.5	±10	0.62	-	-	12	17	15.5	20	20.5	35	SOT-23-3L
YJS8205A	Dual	N	20	5.5	1.25	±10	0.62	-	-	19.5	25	25	32	33	49	SOT-23-6L
YJJ12N02A	Single	N	20	5.5	1.1	±10	0.62	-	-	19.5	25	25	32	33	49	SOT-23-6L
YJS8205B	Dual	N	20	7	1.5	±10	0.62	-	-	13	18	17	22	21	39	SOT-23-6L
YJL3134KW	Single-ESD	N	20	0.75	0.2	±12	0.75	-	-	165	260	215	360	300	700	SOT-323
YJL2102W	Single	N	20	3	0.25	±10	0.78	-	-	57	70	72	98	-	-	SOT-323
YJL3134KDW	Dual-ESD	N	20	0.7	0.2	±12	0.75	-	-	165	260	215	360	300	700	SOT-363
YJL1012E	Single-ESD	N	20	0.77	0.29	±12	0.75	-	-	160	260	211	360	300	700	SOT-523
YJL3134KT	Single-ESD	N	20	0.75	0.18	±12	0.75	-	-	125	260	175	360	275	580	SOT-723
YJH10N02A	Single	N	20	10	1.5	±10	0.62	-	-	7	11	8.5	15	13	20	SOT-89
YJS10N02A	Single	N	20	10	1.9	±10	0.62	-	-	11	13.5	14	17	18.2	25	SOP-8
YJQ2012A	Single	N	20	12	2.5	±10	0.62	-	-	10	13	12.5	16	17	25	DFN2020-6L
YJQ10N02A	Single	N	20	13	2.2	±10	0.62	-	-	7.8	9	9.5	12	12	18.5	DFN2020-6L
YJC2007A	Dual-ESD	N	20	7	1.3	±12	0.62	-	-	13	18	17	22	27	39	DFN2030-6L
YJD30N02A	Single	N	20	30	30	±10	0.62	-	-	5.6	8	7.1	9	10	14	TO-252
YJD60N02A	Single	N	20	60	35	±10	0.62	-	-	4.5	6	5.5	8.8	8	14	TO-252
YJD90N02A	Single	N	20	90	45	±10	0.62	-	-	2.8	4.5	3.3	5	4.7	7.5	TO-252
YJL2304A	Single	N	30	3.6	1	±20	1.5	26	33	39	48	-	-	-	-	SOT-23
YJL3400A	Single	N	30	5.6	1.2	±12	0.9	20	25	23	31	27	45	-	-	SOT-23
YJL3404A	Single	N	30	5.6	1.2	±20	1.5	17	24	26	38	-	-	-	-	SOT-23
YJJ09N03A	Single	N	30	9	1.25	±20	1.5	9	15	12	18	-	-	-	-	SOT-23-6L
YJS3404A	Dual	N	30	8.5	2.5	±20	1.5	14	21	23	35	-	-	-	-	SOP-8
YJS12N03A	Single	N	30	12	2.5	±20	1.5	7	12	11	15	-	-	-	-	SOP-8
YJSD12N03A	Dual	N	30	12	2.5	±20	1.5	7	12	11	15	-	-	-	-	SOP-8
YJS18N03A	Single	N	30	18	3	±20	1.5	4.5	7	6.6	10	-	-	-	-	SOP-8
YJQ3400A	Dual	N	30	7.7	2	±12	0.9	17	23	20	29	24	43	-	-	DFN2020-6L
YJQ13N03A	Single	N	30	13	2.9	±20	1.5	7	12	11	15	-	-	-	-	DFN2020-6L
YJQD12N03A	Dual	N	30	22	12	±20	1.5	12.5	16	24.5	30	-	-	-	-	DFN3333
YJQ30N03A	Single	N	30	30	21	±20	1.5	5.8	9	10	13	-	-	-	-	DFN3333
YJQ3622A	Dual	N	30	30	21	±20	1.5	7.5	13	11.5	16	-	-	-	-	DFN3333
YJQ50N03B	Single	N	30	50	30	±20	1.5	3.9	6	6	8	-	-	-	-	DFN3333
YJQ50N03A	Single	N	30	50	42	±20	1.5	4.9	6	5.9	7	-	-	-	-	DFN3333



中低压MOSFET
LOW AND MEDIUM VOLTAGE MOSFET

N Channel MOS:

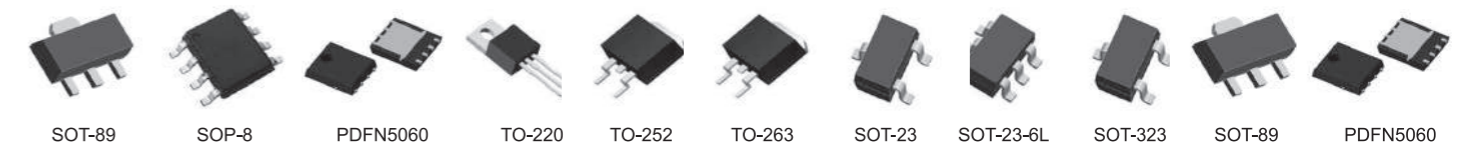
型号 TYPE NO.	结构 Configuration	产品 极性 N/P	漏源电压 V _{oss} (V)	工作 电流 I _d (A)	耗散 功率 Pd	栅源 电压 V _{gs} (V)	阈值 电压 V _{TH} (V)	导通电阻R _{dson} (mΩ) @VGS10V		导通电阻R _{dson} (mΩ) @VGS4.5V		导通电阻R _{dson} (mΩ) @VGS2.5V		导通电阻R _{dson} (mΩ) @VGS1.8V		封装类型 Package
							Typ	Typ	Max	Typ	Max	Typ	Max	Typ	Max	
YJQ60N03A	Single	N	30	60	75	±20	1.5	2	2.5	3	3.8	-	-	-	-	DFN3333
YJG40N03A	Single	N	30	40	21	±20	1.5	5.5	7.5	9.5	11.5	-	-	-	-	PDFN5060
YJG50N03A	Single	N	30	50	45	±20	1.5	3.9	4.7	5	6	-	-	-	-	PDFN5060
YJG105N03A	Single	N	30	105	70	±20	1.5	2.45	3	2.9	4	-	-	-	-	PDFN5060
YJG150N03A	Single	N	30	150	83	±20	1.5	1.58	2	2.6	3.3	-	-	-	-	PDFN5060
YJD50N03A	Single	N	30	50	34	±20	1.5	5.4	7.3	9.5	11.5	-	-	-	-	TO-252
YJD80N03B	Single	N	30	80	45	±20	1.5	3.4	4.9	5.4	7	-	-	-	-	TO-252
YJD80N03A	Single	N	30	80	54	±20	1.5	3.6	4.5	4.7	6	-	-	-	-	TO-252
YJD180N03A	Single	N	30	180	110	±20	1.5	2	2.5	2.85	3.3	-	-	-	-	TO-252
YJL05N04A	Single	N	40	5	1.2	±20	1.5	30	45	40	60	-	-	-	-	SOT-23
YJS10N04A	Single	N	40	10	3	±20	1.5	12.5	15	15.5	24	-	-	-	-	SOP-8
YJSD07N04A	Dual	N	40	7	3	±20	1.5	29.6	36	38.4	51	-	-	-	-	SOP-8
YJQ20N04A	Single	N	40	20	21	±20	1.5	11	14	14.3	18.5	-	-	-	-	DFN3333
YJQ35N04A	Single	N	40	35	40	±20	1.5	6.5	8	8.7	13	-	-	-	-	DFN3333
YJG18N04A	Single	N	40	18	21	±20	1.5	11	14	14	19	-	-	-	-	PDFN5060
YJG90N04A	Single	N	40	90	70	±20	1.2	3.5	4.5	4.4	6.5	-	-	-	-	PDFN5060
YJG100N04A	Single	N	40	100	83	±20	1.5	2.8	3.5	4	4.8	-	-	-	-	PDFN5060
YJP110N04A	Single	N	40	110	125	±20	1.2	3.45	4	4	6	-	-	-	-	TO-220
YJD40N04A	Single	N	40	40	34	±20	1.5	10.6	13	15	23	-	-	-	-	TO-252
YJD60N04A	Single	N	40	60	54	±20	1.5	5.4	7	6.8	9.5	-	-	-	-	TO-252
YJD70N04A	Single	N	40	70	48	±20	1.2	6.5	8	7.7	10	-	-	-	-	TO-252
YJD120N04A	Single	N	40	120	110	±20	1.5	2.8	3.5	4	4.8	-	-	-	-	TO-252
BSS138	Single	N	50	0.34	0.35	±20	1.2	1100	2500	1200	3000	-	-	-	-	SOT-23
BSS138W	Single	N	50	0.34	0.15	±20	1.2	1100	2500	1200	3000	-	-	-	-	SOT-323
BSS138DW	Dual	N	50	0.34	0.35	±20	1.2	1100	2500	1200	3000	-	-	-	-	SOT-363
2N7002K	Single-ESD	N	60	0.34	0.35	±20	1.4	1300	2500	1400	3000	-	-	-	-	SOT-23
2N7002	Single	N	60	0.34	0.35	±30	1.5	1200	2500	1300	3000	-	-	-	-	SOT-23
2N7002A	Single	N	60	0.34	0.35	±30	1.6	1200	2500	1300	3000	-	-	-	-	SOT-23
YJL03N06B	Single	N	60	3	1.2	±16	0.95	86	100	90	120	100	200	-	-	SOT-23
YJL03N06A	Single	N	60	3	1.2	±20	1.3	86	100	92	120	-	-	-	-	SOT-23
YJL05N06AL	Single	N	60	5	2.5	±20	1.5	35	44	39	49	-	-	-	-	SOT-23-3L
2N7002KW	Single-ESD	N	60	0.34	0.35	±20	1.4	1300	2500	1400	3000	-	-	-	-	SOT-323
2N7002W	Single	N	60	0.34	0.15	±30	1.6	1200	2500	1300	3000	-	-	-	-	SOT-323
2N7002DW	Dual	N	60	0.34	0.15	±30	1.6	1200	2500	1300	3000	-	-	-	-	SOT-363
2N7002KDW	Dua-ESD	N	60	0.34	0.35	±20	1.4	1300	2500	1400	3000	-	-	-	-	SOT-363
YJH03N06A	Single	N	60	3	0.69	±20	1.3	86	100	92	120	-	-	-	-	SOT-89



中低压MOSFET
LOW AND MEDIUM VOLTAGE MOSFET

N Channel MOS:

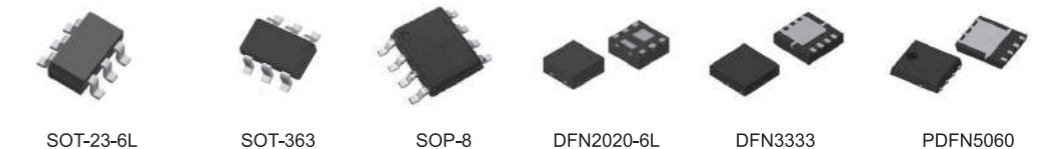
型号 TYPE NO.	结构 Configuration	产品 极性 N/P	漏源电压 V _{oss} (V)	工作 电流 I _d (A)	耗散 功率 Pd	栅源 电压 V _{gs} (V)	阈值 电压 V _{TH} (V)	导通电阻R _{dson} (mΩ) @VGS10V		导通电阻R _{dson} (mΩ) @VGS4.5V		导通电阻R _{dson} (mΩ) @VGS2.5V		导通电阻R _{dson} (mΩ) @VGS1.8V		封装类型 Package
							Typ	Typ	Max	Typ	Max	Typ	Max	Typ	Max	
YJH03N06B	Single	N	60	3.5	1.7	±16	0.95	86	100	90	120	100	200	-	-	SOT-89
YJS05N06A	Dual	N	60	5	3.1	±20	1.5	35	44	39	49	-	-	-	-	SOP-8
YJS4438A	Single	N	60	8.2	3.1	±20	1.5	14.5	22	17	34	-	-	-	-	SOP-8
YJG20N06A	Single	N	60	20	21	±20	1.5	34	43	36	47	-	-	-	-	PDFN5060
YJG30N06A	Single	N	60	30	45	±20	1.5	16	20	17.5	23	-	-	-	-	PDFN5060
YJP150N06AQ	Single	N	60	150	225	±20	3	4.6	5.5	-	-	-	-	-	-	TO-220
YJR20N06A	Single	N	60	20	34	±20	1.5	29	43	31	47	-	-	-	-	TO-251
YJD20N06A	Single	N	60	20	34	±20	1.5	34	43	36	47	-	-	-	-	TO-252
YJD90N06A	Single	N	60	90	110	±20	1.5	5.6	7.2	6.8	8.5	-	-	-	-	TO-252
YJB150N06C	Single	N	60	150	225	±20	3	4.6	5.5	-	-	-	-	-	-	TO-263
BSS123	Single	N	100	0.2	0.35	±20	1.8	3000	5000	3500	5500	-	-	-	-	SOT-23
YJL01N10A	Single	N	100	1.5	1.2	±20	1.8	430	500	460	550	-	-	-	-	SOT-23
YJL02N10A	Single	N	100	2	1.3	±20	1.8	250	280	260	310	-	-	-	-	SOT-23
YJS03N10A	Single	N	100	3	1.5	±20	1.8	95	120	100	140	-	-	-	-	SOT-23-6L
BSS123W	Single	N	100	0.2	0.15	±20	1.8	3000	5000	3500	5500	-	-	-	-	SOT-323
YJH03N10A	Single	N	100	3	1.5	±20	1.8	95	110	100	120	-	-	-	-	SOT-89
YJG18N10A	Single	N	100	18	45	±20	1.8	49	60	52	70	-	-	-	-	PDFN5060
YJD15N10A	Single	N	100	15	34	±20	1.8	95	110	100	120	-	-	-	-	TO-252
YJD25N10A	Single	N	100	25	54	±20	1.8	43	52	46	56	-	-	-	-	TO-252



中低压MOSFET
LOW AND MEDIUM VOLTAGE MOSFET

N+P Complementary MOS:

型号 TYPE NO.	结构 Configuration	产品 极性 N/P	漏源电压 V _{oss} (V)	工作 电流 I _d (A)	耗散 功率 Pd	栅源 电压 V _{gs} (V)	阈值 电压 V _{TH} (V)	导通电阻R _{dson} (mΩ) @VGS10V		导通电阻R _{dson} (mΩ) @VGS4.5V		导通电阻R _{dson} (mΩ) @VGS2.5V		导通电阻R _{dson} (mΩ) @VGS1.8V		封装类型 Package
							Typ	Typ	Max	Typ	Max	Typ	Max	Typ	Max	
YJS2308A	Dual	N/P	20	5.6	1.3	±10	0.62	-	-	19.5	25	25	32	33	49	SOT-23-6L
YJL3439KDW	Dual -ESD	N/P	20	0.74	0.2	±12	0.75	-	-	161	260	213	360	305	700	SOT-363
			-20	-0.65	0.2		-0.75	397	520	541	750	746	1300			
YJS4606A	Dual	N/P	30	6.0	2.0	±20	1.5	21	29	27	40	-	-	-	-	SOP-8
			-30	-5.0	2.0		-1.5	40	55	53	68	-	-	-	-	
YJS07NP03A	Dual	N/P	30	7.0	1.9	±20	1.5	14	20	20	35	-	-	-	-	SOP-8
			-30	-7.0	1.9		-1.5	16	23	21.5	34	-	-	-	-	
YJQC602B	Dual	N/P	20	6.0	1.8	±10	0.62	-	-	19.5	25	25	32	33	49	DFN2020-6L
			-20	-6.0	2.2		-0.62	33	42	39	55	49	75			
YJQ3611A	Dual	N/P	30	3.6	2.0	±20	1.5	30	39	40	52	-	-	-	-	DFN3333
			-30	-5.0	2.0		-1.5	40	55	53	68	-	-	-	-	
YJQ4606A	Dual	N/P	30	6.0	2.0	±20	1.5	21	29	27	40	-	-	-	-	DFN3333
			-30	-5.0	2.0		-1.5	40	55	53	68	-	-	-	-	
YJG40NP03A	Dual	N/P	30	40	21	±20	1.5	8	10	12	14	-	-	-	-	DFN5060
			-30	-40	35		-1.8	13	17	17	27	-	-	-	-	



中低压MOSFET LOW AND MEDIUM VOLTAGE MOSFET

SGT N Channel MOS:

型号 TYPE NO.	结构 Configuration	产品 极性 N/P	漏源电压 V _{DSS} (V)	工作 电流 I _d (A)	耗散 功率 P _d	栅源 电压 V _{GS} (V)	阈值电压 V _{TH} (V)		导通电阻R _{dson} (mΩ) @V _{GS} 10V		导通电阻R _{dson} (mΩ) @V _{GS} 4.5V		封装类型 Package
							Typ	Max	Typ	Max	Typ	Max	
YJG130G04AR	Single	N	40	130	149	±20	1.8	0.9	1.1	1.5	2	PDFN5060	
YJS12G06A	Single	N	60	12	3.1	±20	1.7	8.2	9	10.5	13	SOP-8	
YJQ53G06A	Single	N	60	53	45	±20	1.7	7.2	8.2	9.1	12	DFN3333	
YJG53G06A	Single	N	60	53	65	±20	1.7	6.8	8.2	9.5	12	PDFN5060	
YJG80G06A	Single	N	60	80	96	±20	1.7	3.5	4.2	4.2	5.2	PDFN5060	
YJG95G06A	Single	N	60	95	120	±20	1.6	2.1	2.5	2.7	3.4	PDFN5060	
YJG95G06AR	Single	N	60	95	120	±20	1.6	1.7	2.5	2.4	3.4	PDFN5060	
YJG95G06B	Single	N	60	95	120	±20	2.8	2.25	2.9	-	-	PDFN5060	
YJP200G06A	Single	N	60	200	260	±20	1.6	2.35	2.9	2.9	3.6	TO-220	
YJP200G06B	Single	N	60	200	260	±20	2.8	2.5	2.9	-	-	TO-220	
YJD80G06A	Single	N	60	80	78	±20	1.7	6.6	8	8.2	11	TO-252	
YJB200G06A	Single	N	60	200	260	±20	1.6	2.35	2.6	2.9	3.6	TO-263	
YJB200G06B	Single	N	60	200	260	±20	2.8	2.3	2.9	-	-	TO-263	
YJL03G10A	Single	N	100	3	1.2	±20	1.8	110	140	160	300	SOT-23	
YJS12G10A	Single	N	100	12	3.1	±20	2.8	14.5	17	-	-	SOP-8	
YJS15G10A	Single	N	100	15	3.8	±20	1.8	8	9.5	9.7	12.5	SOP-8	
YJS15G10C	Single	N	100	15	3.8	±20	2.8	8	9.5	-	-	SOP-8	
YJQ40G10A	Single	N	100	40	43	±20	1.8	15	18.5	18	22.5	DFN3333	
YJGD20G10A	Dual	N	100	20	17	±20	1.8	17	22	21	27	DFN5060	
YJG40G10A	Single	N	100	40	60	±20	1.8	14	17.5	17	21.5	PDFN5060	
YJG60G10A	Single	N	100	60	88	±20	2.8	7.2	8.6	-	-	PDFN5060	
YJP45G10B	Single	N	100	45	100	±20	2.8	14	17	-	-	TO-220	
YJP70G10A	Single	N	100	70	125	±20	1.8	7.2	8.6	8.8	11	TO-220	
YJP70G10B	Single	N	100	70	125	±20	2.8	7.2	8.6	-	-	TO-220	
YJD45G10A	Single	N	100	45	72	±20	1.8	14	17	17	21.5	TO-252	
YJD45G10B	Single	N	100	45	72	±20	2.8	14	17	-	-	TO-252	
YJB70G10A	Single	N	100	70	125	±20	1.8	7.2	8.6	8.8	11	TO-263	
YJB70G10B	Single	N	100	70	125	±20	2.8	7.2	8.6	-	-	TO-263	
YJJ03G10A	Single	N	110	3	1.5	±20	1.8	110	140	135	250	SOT-23-6L	
YJS05N15B	Single	N	150	4.6	3.1	±20	2	63	75	70	88	SOP-8	
YJG15N15B	Single	N	150	15	45	±20	2	63	75	70	88	PDFN5060	
YJG85G15A	Single	N	150	85	120	±20	3.5	11	15	-	-	PDFN5060	
YJP25N15B	Single	N	150	25	52	±20	2	63	75	70	88	TO-220F	
YJD25N15B	Single	N	150	25	52	±20	2	63	75	70	88	TO-252	
YJB145G15A	Single	N	150	145	357	±20	3.5	6.2	8	-	-	TO-263	



中低压MOSFET LOW AND MEDIUM VOLTAGE MOSFET

SGT P Channel MOS:

型号 TYPE NO.	结构 Configuration	产品 极性 N/P	漏源电压 V _{DSS} (V)	工作 电流 I _d (A)	耗散 功率 P _d	栅源 电压 V _{GS} (V)	阈值电压 V _{TH} (V)		导通电阻R _{dson} (mΩ) @V _{GS} 10V		导通电阻R _{dson} (mΩ) @V _{GS} 4.5V		封装类型 Package
							Typ	Max	Typ	Max	Typ	Max	
YJS03GP10A	Single	P	-100	-3.1	3.1	±20	-1.8	132	170	145	200	SOP-8	
YJQ15GP10A	Single	P	-100	-15	43	±20	-1.8	78	95	87	110	DFN3333	
YJG15GP10A	Single	P	-100	-15	60	±20	-1.8	75	90	85	110	PDFN5060	
YJG25GP10A	Single	P	-100	-25	88	±20	-1.8	38	48	43	55	PDFN5060	
YJP30GP10A	Single	P	-100	-30	125	±20	-1.8	38	48	43	55	TO-220	
YJD18GP10A	Single	P	-100	-18	72	±20	-1.8	75	90	85	110	TO-252	
YJB30GP10A	Single	P	-100	-30	125	±20	-1.8	38	48	43	55	TO-263	
YJQ23GP06A	Single	P	-60	-23	43	±20	-2.1	30	40	41	55	DFN3333	
YJG28GP06A	Single	P	-60	-28	60	±20	-2.1	30	40	41	55	PDFN5060	
YJD30GP06A	Single	P	-60	-30	72	±20	-2.1	30	40	41	55	TO-252	

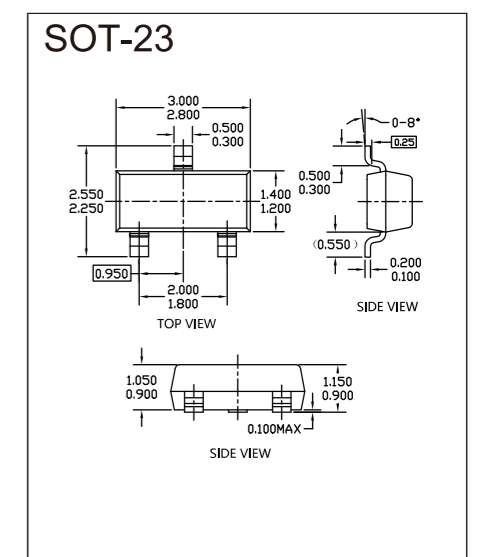
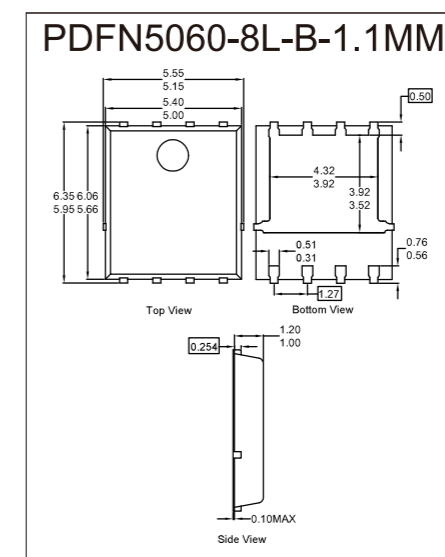
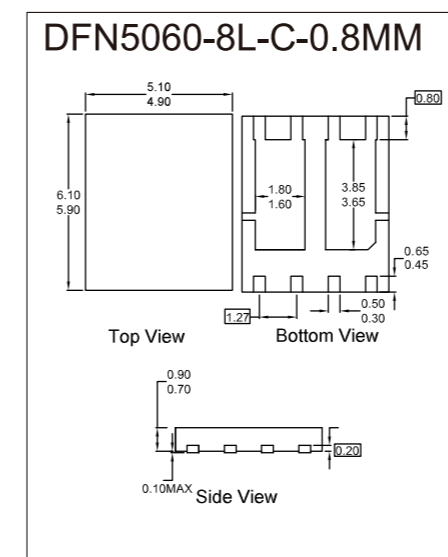
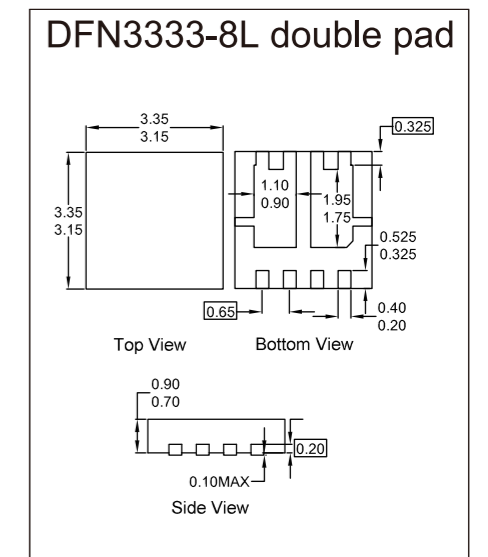
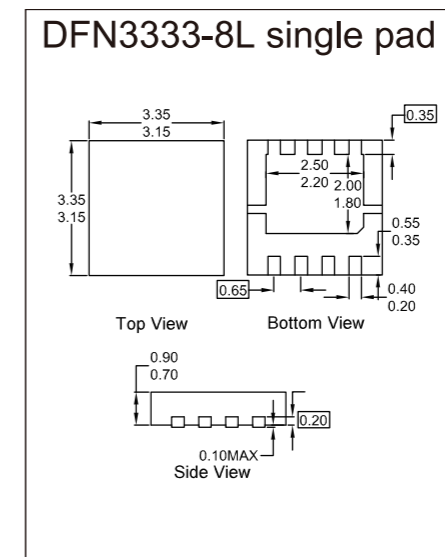
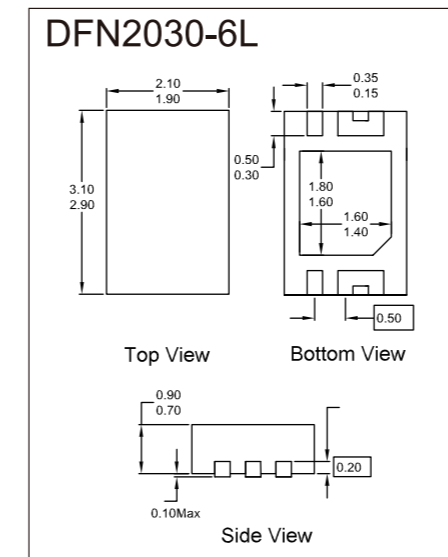
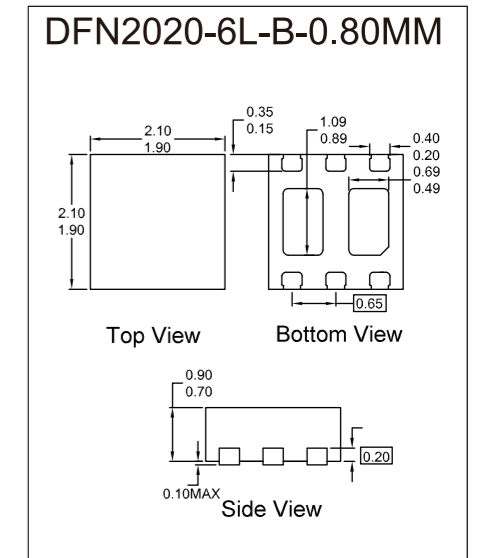
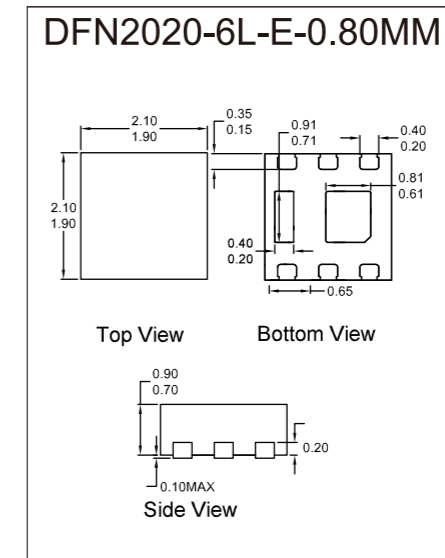
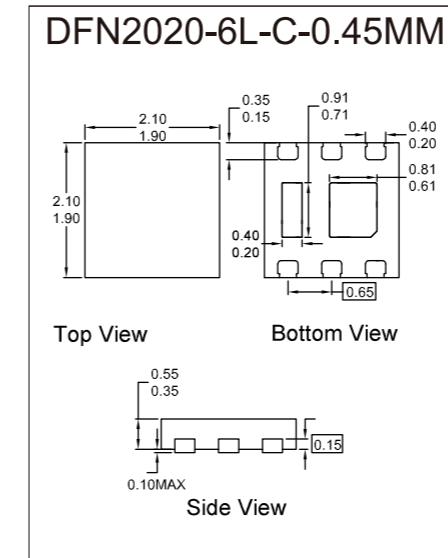


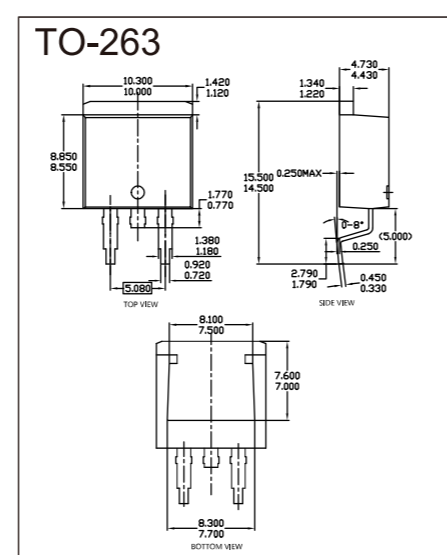
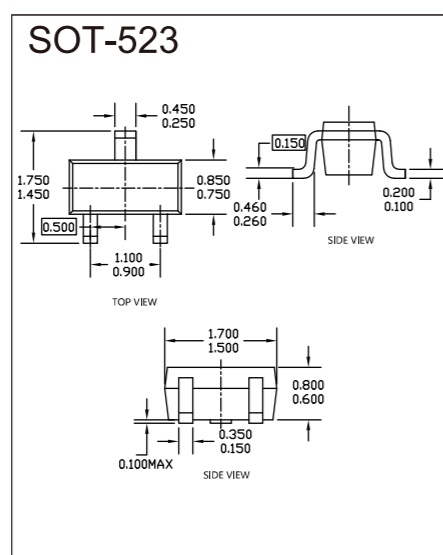
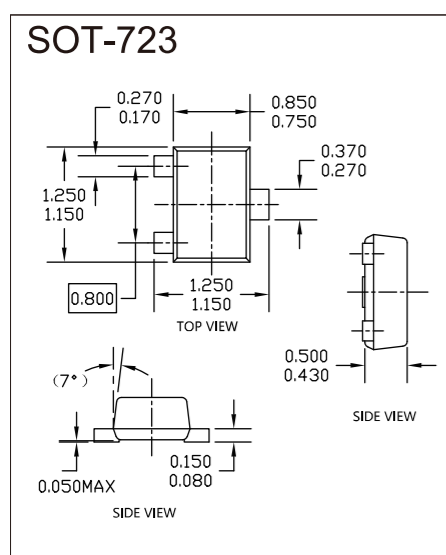
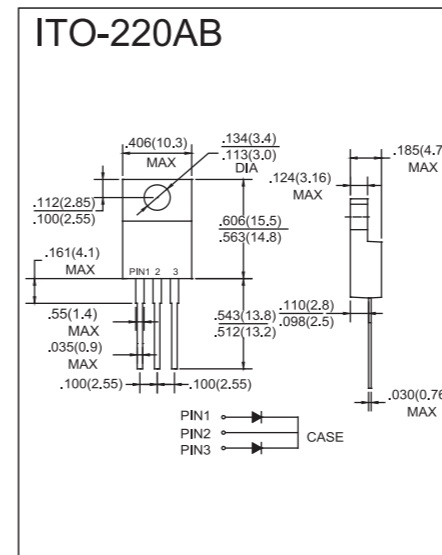
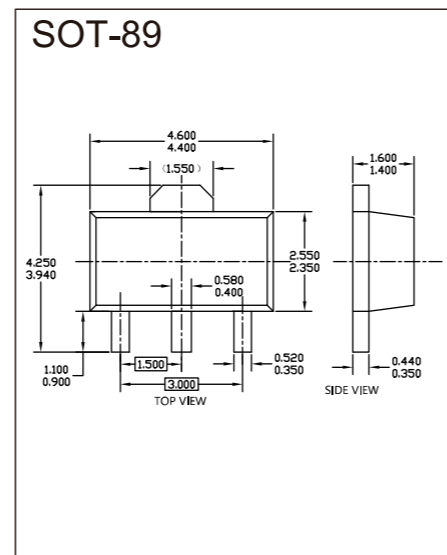
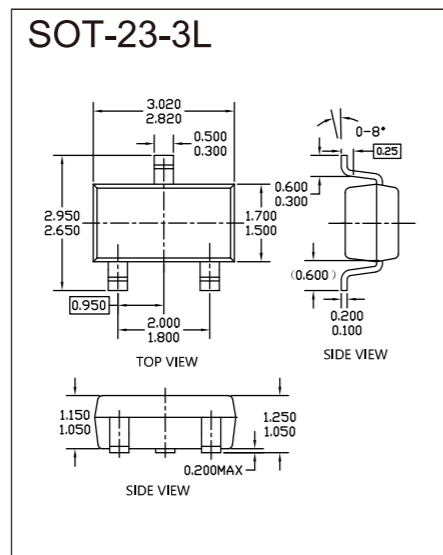
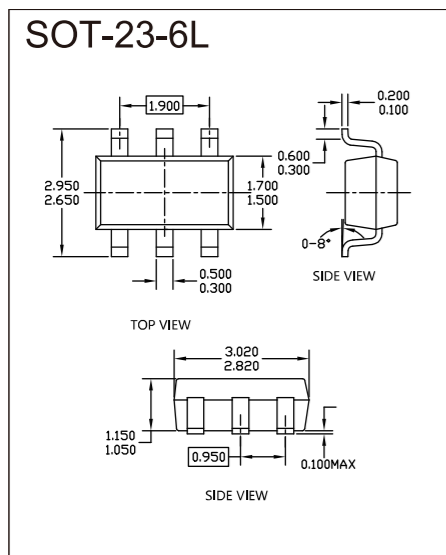
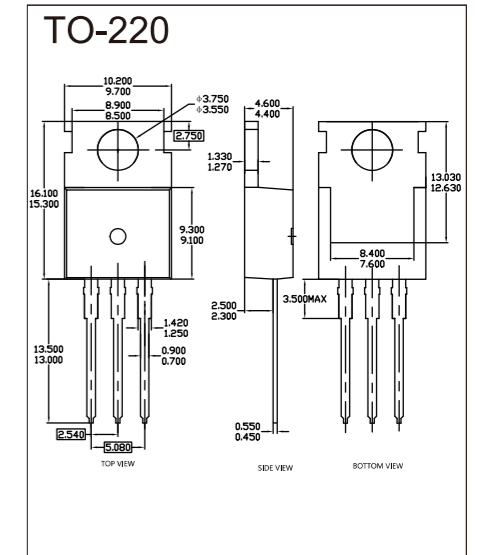
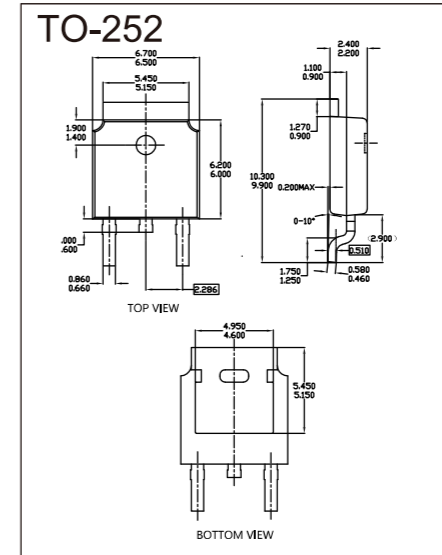
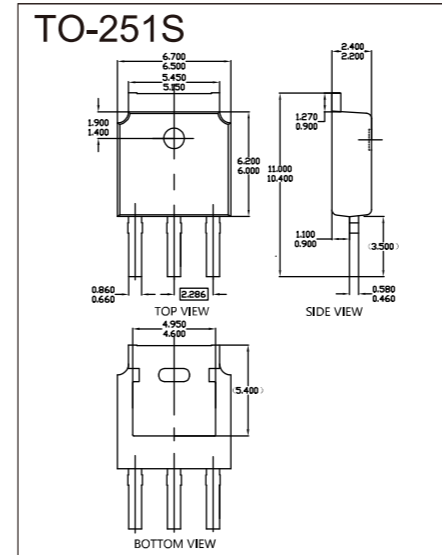
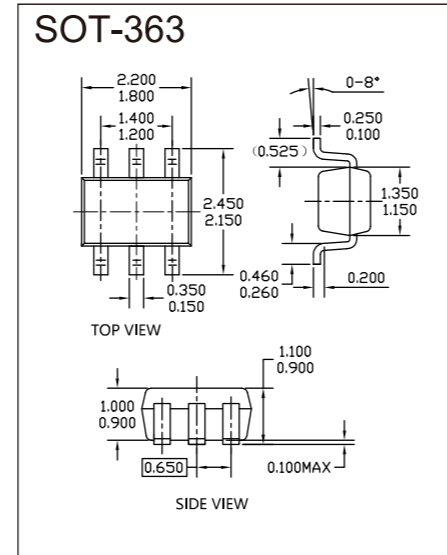
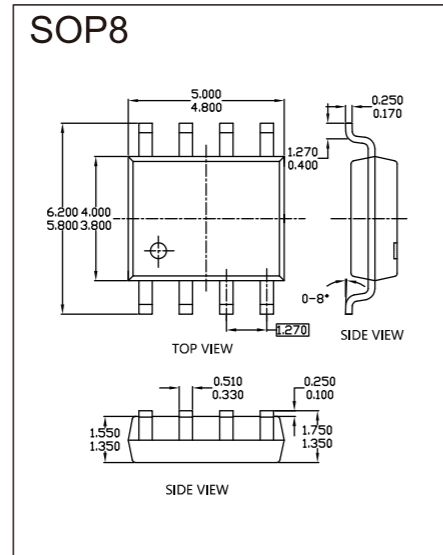
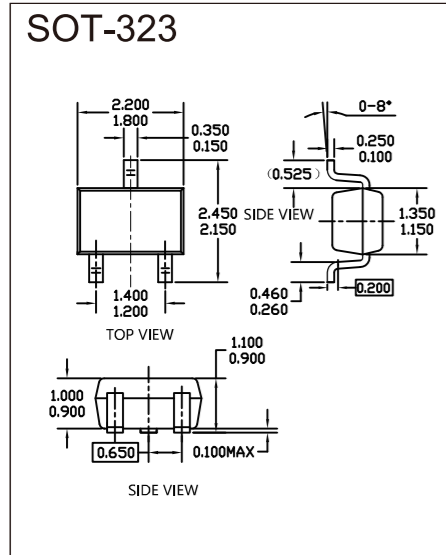
高压MOSFET
HIGH VOLTAGE MOSFET

型号 TYPE NO.	漏电流 I _b (A)			漏源耐压 B _v DSS (V)		导通电阻 R _{DS(on)} (Ω)		阈值电压 V _{TH} (V)			栅源电压 V _{GS} (V)	漏源漏电流 I _{BSS} (μA)	栅源漏电流 I _{GSS} (nA)	封装 Package
	Max	Min	Typ	Typ	Max	Min	Typ	Max	Max	Max	Max	Max		
YJ2N60Z	2	600	630	3.6	4.2	2	3	4	±30	1	100	TO-252		
YJ4N60Z	4	600	630	1.9	2.4	2	3	4	±30	1	100	TO-220AB		
YJ7N60Z	7	600	630	1	1.3	2	3	4	±30	1	100	ITO-220AB		
YJ2N65Z	2	650	670	3.7	4.8	2	3	4	±30	1	100	TO-220AB		
YJ4N65Z	4	650	670	2	2.5	2	3	4	±30	1	100	ITO-220AB		
YJ7N65Z	7	650	670	1.1	1.4	2	3	4	±30	1	100	TO-220AB		
YJ8N60Z	8	600	630	0.9	1.3	2	3	4	±30	1	100	ITO-220AB		
YJ10N60Z	10	600	630	0.7	0.75	2	3	4	±30	1	100	TO-220AB		
YJ12N60Z	12	600	630	0.6	0.65	2	3	4	±30	1	100	ITO-220AB		
YJ8N65Z	8	650	670	1	1.4	2	3	4	±30	1	100	TO-220AB		
YJ10N65Z	10	650	670	0.75	0.8	2	3	4	±30	1	100	ITO-220AB		
YJ12N65Z	12	650	670	0.65	0.75	2	3	4	±30	1	100	TO-220AB		
YJ4N70Z	4	700	730	2.4	2.8	2	3	4	±30	1	100	ITO-220AB		
YJ7N70Z	7	700	730	1.4	1.6	2	3	4	±30	1	100	TO-220AB		
YJ10N70Z	10	700	730	1	1.2	2	3	4	±30	1	100	ITO-220AB		
YJ12N70Z	12	700	730	0.9	1.1	2	3	4	±30	1	100	TO-220AB		
YJ4N80Z	4	800	830	3	3.8	2	3	4	±30	1	100	ITO-220AB		
YJ7N80	7	800	830	2.2	2.6	2	3	4	±30	1	100	TO-220AB		

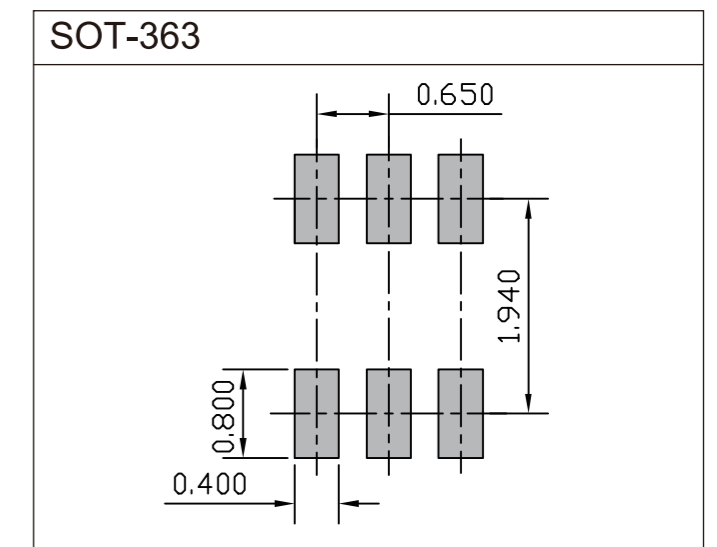
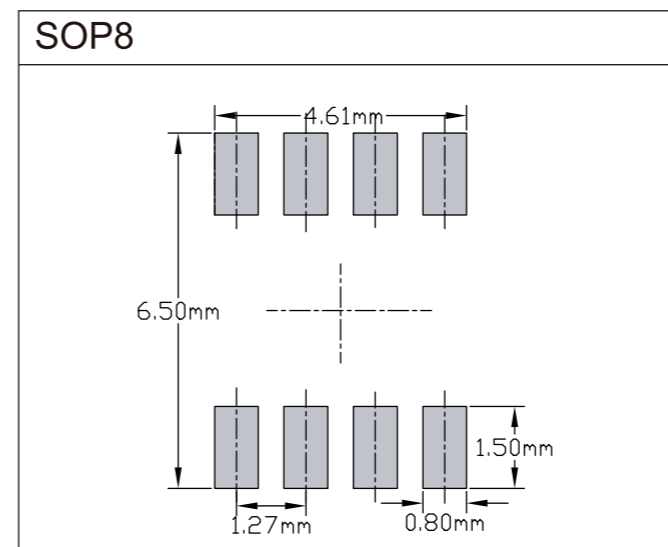
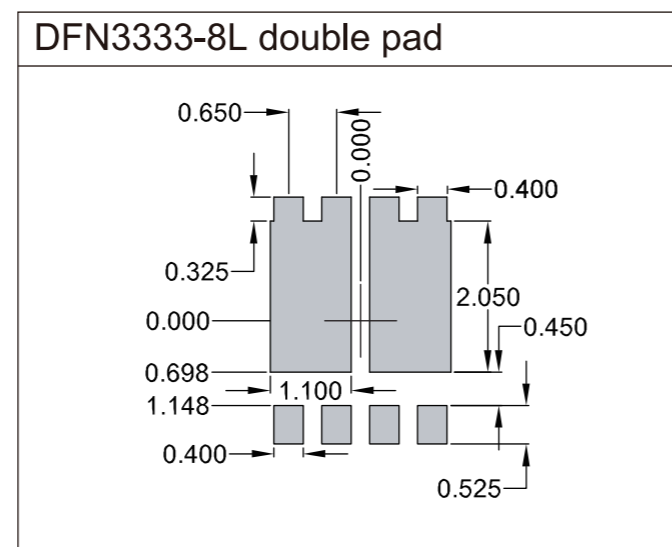
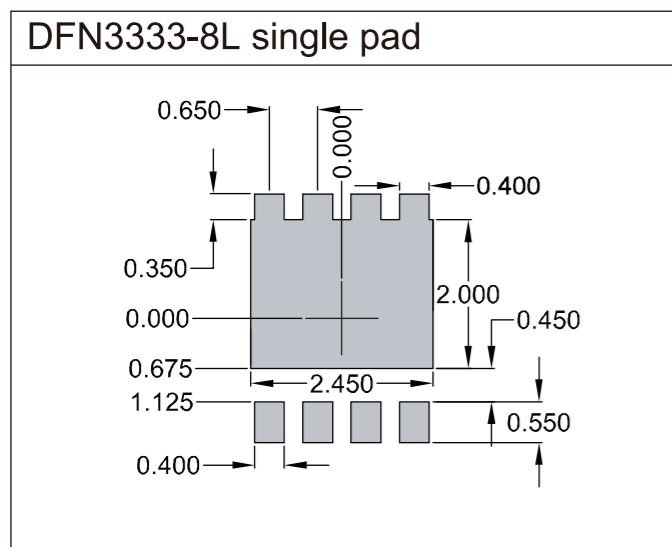
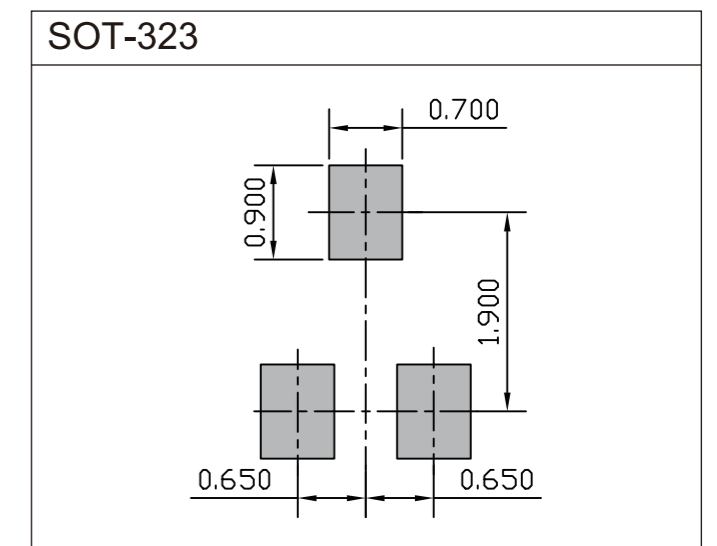
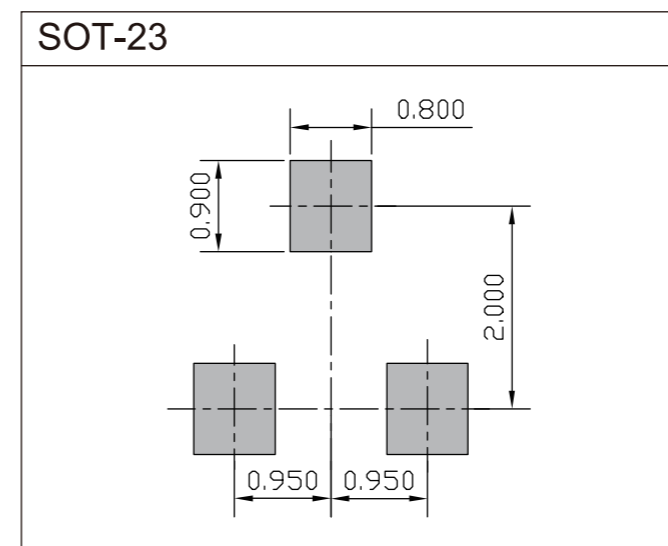
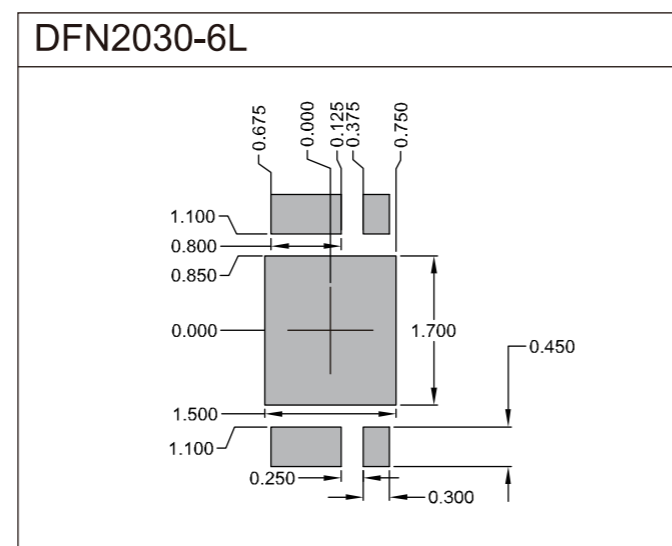
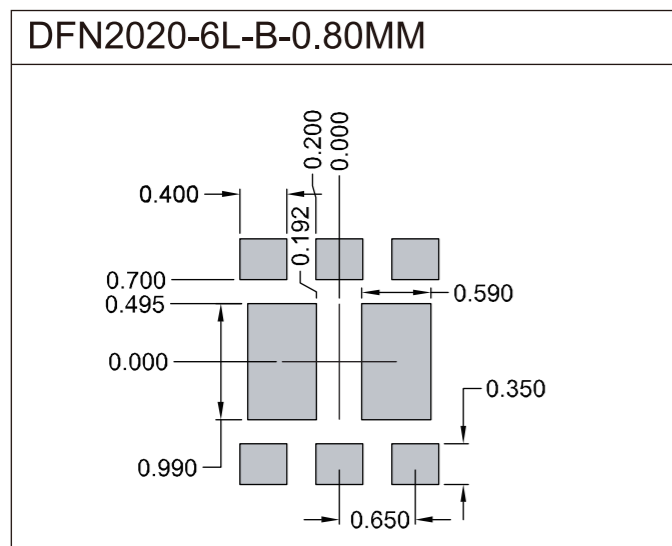
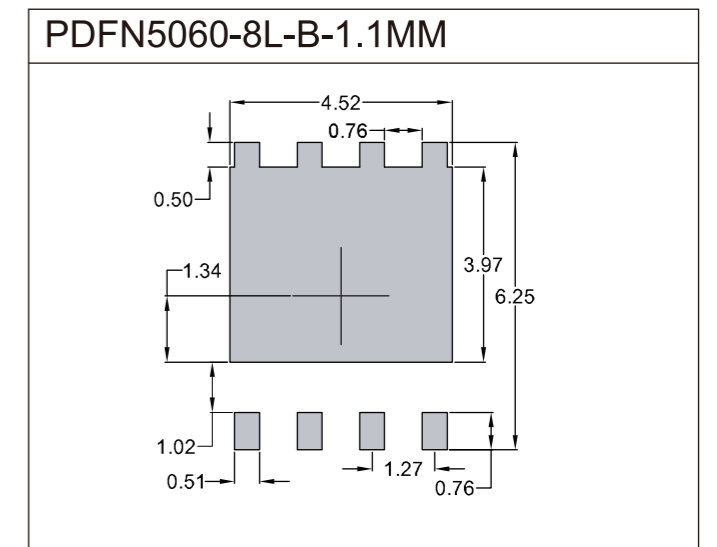
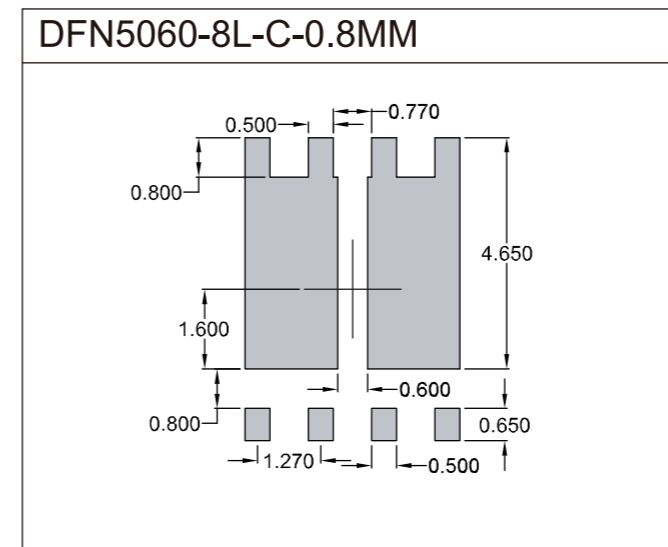
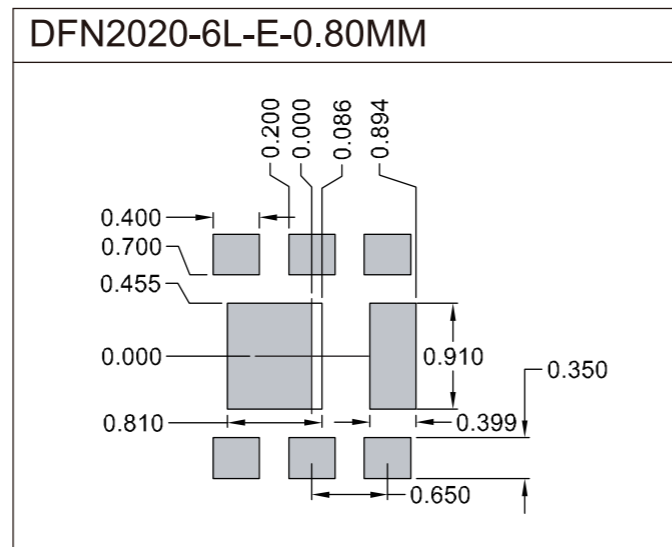
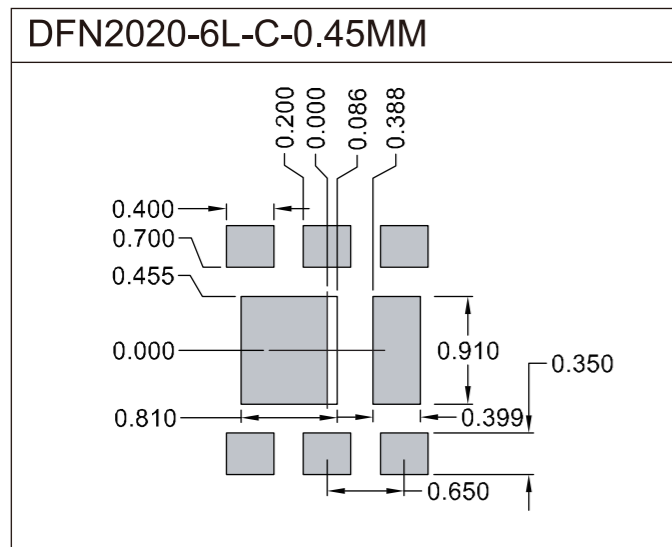


封装尺寸图 (单位: mm)
OUTLINE DRAWING

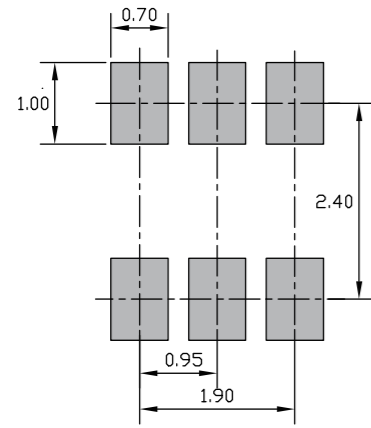




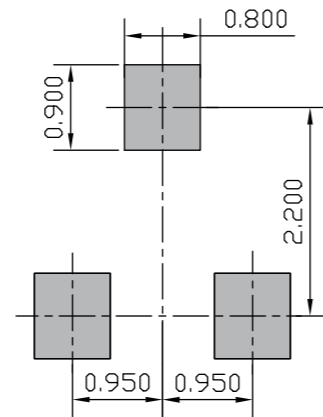
焊盘尺寸图 (单位: mm)
SUGGESTED PAD LAYOUT



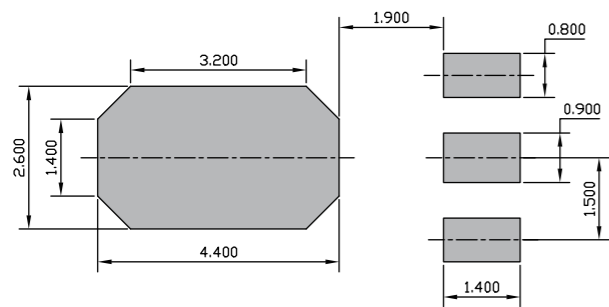
SOT-23-6L



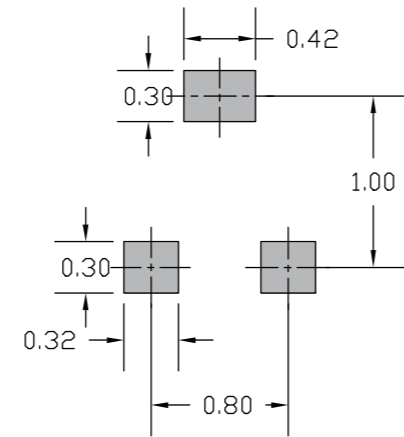
SOT-23-3L



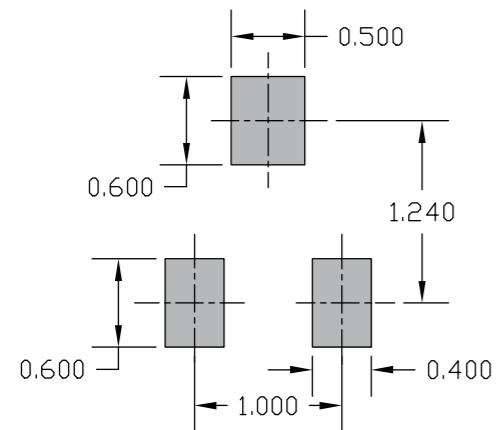
SOT-89



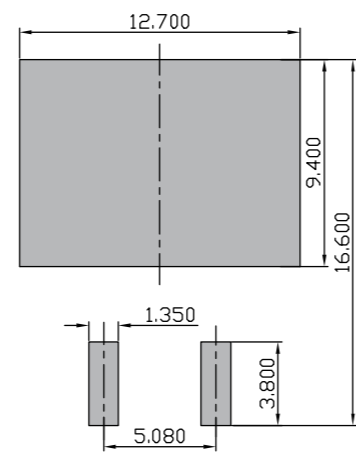
SOT-723



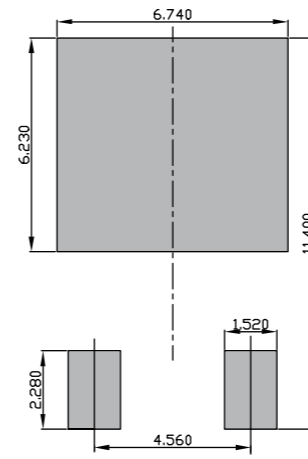
SOT-523



TO-263

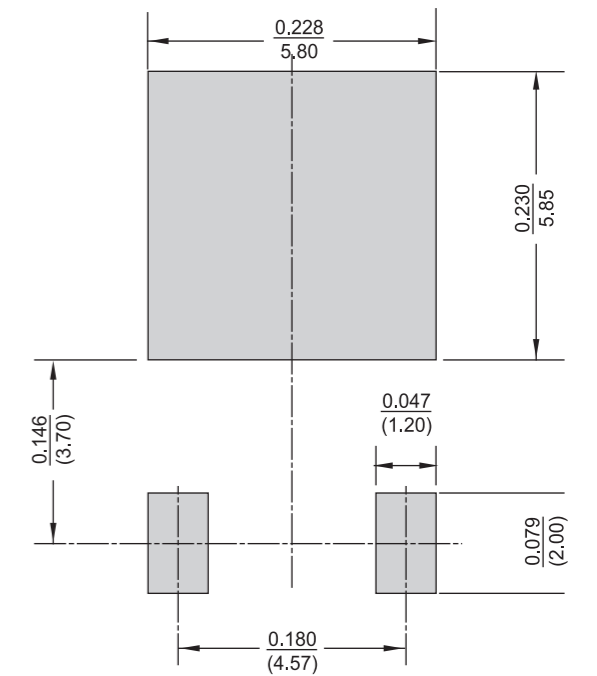


TO-252



TO-252

Unit: inch(mm)



包装形态 PACKING

封装型号 Package No	包装代码 Packing Code	包装方式 Packing Method	PCS/(管或卷) Tube/Reel	只/盒 Pcs/Box	只/箱 Pcs/ Carton	料管尺寸 (mm) Tube Size			内盒尺寸 (mm) Carton Size			外箱尺寸 (mm) Single box weight			单盒重量 (±0.3Kg) 毛重(KG) 净重(KG)		整箱重量 (±0.5Kg) 毛重(KG) 净重(KG)	
						长(L)	宽(W)	高(H)	长(L)	宽(W)	高(H)	长(L)	宽(W)	高(H)	毛重(KG)	净重(KG)	毛重(KG)	净重(KG)
DFN2020-6L-C-0.45MM	F1	Reel	3000	30000	1200000	/	/	/	230	145	202	470	305	223	1.38	0.18	6.13	0.73
DFN2020-6L-E-0.80MM single pad	F1	Reel	3000	30000	1200000	/	/	/	230	145	202	470	305	223	1.50	0.30	6.60	1.20
DFN2020-6L-B-0.80MM double pad	F1	Reel	3000	30000	1200000	/	/	/	230	145	202	470	305	223	1.50	0.30	6.60	1.20
DFN2030-6L	F1	Reel	3000	30000	1200000	/	/	/	230	145	202	470	305	223	1.60	0.46	7.02	1.83
DFN3333-8L single pad	F1	Reel	5000	10000	100000	/	/	/	350	337	40	450	370	360	1.35	0.27	14.33	2.73
DFN3333-8L double pad	F1	Reel	5000	10000	100000	/	/	/	350	337	40	450	370	360	1.35	0.27	14.33	2.73
DFN5060-8L-C-0.8MM	F1	Reel	5000	10000	100000	/	/	/	350	337	40	450	370	360	2.11	0.77	21.90	7.70
PDFN5060-8L	F1	Reel	5000	10000	100000	/	/	/	350	337	40	450	370	360	2.11	1.03	21.90	10.30
SOT-23	F2	Reel	3000	30000	120000	/	/	/	210	210	215	440	440	230	1.48	0.30	7.0	1.2
SOT-323	F2	Reel	3000	30000	120000	/	/	/	210	210	215	440	440	230	1.31	0.14	6.3	0.6
SOP-8	F2	Reel	4000	8000	64000	/	/	/	360	336	60	520	390	360	1.56	0.7	12.5	5.57
SOT-363	F2	Reel	3000	30000	120000	/	/	/	210	210	215	440	440	230	1.24	0.27	5.9	1.08
SOT-23-6L	F2	Reel	3000	30000	120000	/	/	/	210	210	215	440	440	230	1.58	0.48	6.9	1.92
SOT-23-3L	F1	Reel	3000	30000	120000	/	/	/	210	210	215	440	440	230	1.51	0.41	6.6	1.64
SOT-89	F1	Reel	1000	10000	40000	/	/	/	210	210	220	460	445	240	1.59	0.49	6.4	1.96
SOT-723	F1	Reel	8000	80000	320000	/	/	/	210	210	210	440	440	230	1.21	0.11	5.7	0.44
SOT-523	F2	Reel	3000	30000	120000	/	/	/	210	210	215	440	440	230	1.18	0.08	5.2	0.32
TO-263	F1	Reel	1000	2000	10000	/	/	/	400	390	70	430	410	375	3.95	2.8	20.8	14.1
	F2	Reel	800	1600	8000	/	/	/	335	335	65	370	350	350	3.15	2.26	16.7	11.3
	B1	Tube	50	2000	8000	530	31.9	6.5	545	145	87	575	330	210	4.39	2.8	18.8	11.3
TO-251	B1	Tube	75	4500	22500	517	20	3.5	555	150	45	570	255	170	2.9	1.62	15.05	8.1
TO-252	F1/F2	Reel	2500	2500	25000	/	/	/	345	345	26	380	290	365	2.54	1.5	13.62	7.5
TO-220	B1	Tube	50	1000	5000	532	33	7	570	255	170	570	255	170	2.8	2	14	10
ITO-220AB	B1	Tube	50	1000	5000	532	33	7	570	255	170	570	255	170	2.8	2	14	10

可靠性试验项目 RELIABILITY TEST ITEM

序号	试验项目 Test Item	试验条件 Condition	参考标准 Reference	实验时间 (Time)	适用范围 (Scope)
1	预处理 (Pre-conditioning)	Performed on surface mount devices (SMDs) prior to TC,AC, H3TRB/HAST & IOL/PTC stresses only.	JESD22-A113	1.Temperature Cycling:-40 C~60 C, 5cycles; 2.Bake:125 C,24H; 3.Moisture Soak:85±2 C, 85±5%/168h; 4.Reflow*3cycles:260 C,3cycles time 5-60min	Only For SMD Series 仅适用于贴片系列
2	高温反偏 (High Temperature Reverse Bias)	Tjmax,80%VR(Zener 100%Vz,TVS 100%Vrwm)	JESD22-A108	1000Hrs	All Series 所有系列
3	高温栅极偏压 (High Temperature Gate Bias)	Tjmax,100%Vgs	JESD-A108	1000Hrs	Only For MOS 仅适用于MOS产品
4	间歇老化 (Intermittent Operational Life)	△Tj≥100 C,2min ON/2min OFF	MIL-STD-750 Method 1037	15000Cycles	Except for TVS&Zener Series TVS&Zener不适用
5	高温高湿反偏 (High-temperature High-humidity Reverse Bias)	85±2 C, 85%±5%RH, 80%VR (Max=100V)	JESD22-A101	1000Hrs	All Series 所有系列
6	高加速寿命实验 (Highly Accelerated Stress Test)	130±2 C, 85%±5%RH 80%VR (Max=42V)	JESD22-A110	96Hrs	All Series 所有系列
7	高温高湿 (High-temperature High-humidity storage test)	85±2 C, 85±5%RH	MIL-STD-202F METHOD-103B	1000Hrs	All Series 所有系列
8	温度循环试验 (Temperature Cycling)	150 C (+15, -0) /15min, -55 C (+0, -10) /15min	JESD22-A104	1000 cycles	All Series 所有系列
9	高温储存 (High Temperature Storage)	150 C (+10, -0)	JESD22-A103	1000Hrs	All Series 所有系列
10	低温储存 (Low Temperature storage)	-55 C	Specification	1000Hrs	All Series 所有系列
11	高压蒸煮 (Auto-clave)	121 C±2 C,15 psig,100%RH	JESD22-A102	96Hrs	All Series 所有系列
12	盐雾试验 (Salt Spray Test)	试验温度: 35±2 C, 氯化钠盐水浓度: 5±0.1%, PH值范围: 6.5-7.2, 沉降率: 1~2ml/80cm².h	GB/T 2423.17-2008	24Hrs	All Series 所有系列
13	易焊性试验 (Solderability)	235 C±5 C	J-STD-002	3sec	All Series 所有系列
14	耐焊接热 (Resistance to solder heat)	DIP: 270±5 C SMD: 260 C (+5,-0)	JESD22-B106 JESD22-A111	DIP: 7sec(+2, -0) SMD :10sec	All Series 所有系列
15	弯曲牢度 (Bending Strength)	φ0.6mm~0.78mm W=0.5Kg >φ1.20mm W=2Kg	MIL-STD-750 Method 2036	90±5° 3Times	Axial Series 插件系列
16	终端牢度 (Terminal Strength)	φ0.6mm~φ0.78mm W=1Kg >φ1.20mm W=3Kg	MIL-STD-750 Method 2036	15sec	Axial Series 插件系列
17	正向浪涌试验 (Forward Surge Test)	8.3ms,Single,Half-Wave	MIL-STD-750 Method 4066	5Times	All Series 所有系列
18	静电测试 (ESD)	HBM: 100pF,1500Ω ,GPP:4KV; Others:2KV; MM: 200pF,0Ω ,400V	AEC-Q101-001/002	1cycle	All Series 所有系列



销售网络

◆扬州办事处

Add: 扬州市维扬经济开发区荷叶西路6号
Tel: 0086-514-87948506
Email: haiyang.zhu@21yangjie.com

◆上海办事处

Add: 上海市虹桥商务区申虹路666号正荣中心1号楼503
Tel: 0086-21-64661571
Email: zhijuan.zhan@21yangjie.com

◆杭州办事处

Add: 杭州市滨江区长河街道科技馆街1600号银泰国际商务中心2706室
Tel: 0086-571-87552171
Email: mj@21yangjie.com

◆深圳办事处

Add: 深圳市宝安区西乡大道230号满京华艺峦大厦1座16楼
Tel: 0086-755-61200115
Email: changhao.li@21yangjie.com

◆广州办事处

Add: 广州市番禺区钟村雄峰城G5座313室
Tel: 0086-20-81375959
Email: jing.sun@21yangjie.com

◆厦门办事处

Add: 厦门市湖里区象屿保税区银盛大厦10D
Tel: 0086-592-5600175
Email: zb@21yangjie.com

◆武汉办事处

Add: 武汉市江夏区武大园三路力源信息203
Tel: 0086-27-87166707
Email: leo.liao@21yangjie.com

◆成都办事处

Add: 成都市金牛区兴盛西路2号天元大厦2-511室
Tel: 0086-28-87751036
Email: fei.long@21yangjie.com

◆天津办事处

Add: 天津市武清区雍阳西路莱茵翠景3-1-201
Tel: 0086-22-58952318
Email: guangwei.cheng@21yangjie.com

◆青岛办事处

Add: 青岛市李沧区书院路37号奥克斯广场6号楼1702室
Tel: 0086-532-66760079
Email: huanjian.liu@21yangjie.com

◆台湾办事处

Add: 新北市中和区建八路16号六楼-5
电话: 886-82263996
Email: stanley.yeh@21yangjie.com

◆South Korea Sales Office

Add: Rm 1105,Bd 103,No.88, Sinwon-ro, Yeongtong-gu, Suwon-si, Gyeonggi-do, Republic of Korea
Tel: 070-8890-0188
Email: sunny.qian@21yangjie.com

◆Japan Sales Office

Add: 东京都中央区日本桥兜町5-1兜町第1平和ビル3F
Tel: 0086-514-80983686
Email: yjsale7@21yangjie.com

◆South Asia and India Sales Office

Add: No. 6,West Heye Road, Hanjiang District, Yangzhou, China
Tel: 0086-86-514-80982407
Email: yjdiode@21yangjie.com

◆光伏销售部

Add: 扬州市维扬经济开发区荷叶西路6号
Tel: 0086-514-80982898
Email: zgj@21yangjie.com

◆MOS销售部

Add: 扬州市维扬经济开发区荷叶西路6号
Tel: 0086-514-80982898
Email: yjrd02@21yangjie.com

◆模块销售部

Add: 扬州市维扬经济开发区荷叶西路6号
Tel: 0514-80981368
Email: xingquan.li@21yangjie.com

◆晶圆销售部

Add: 扬州市维扬经济开发区创业园中路26号
Tel: 0514-80982389
Email: yzbb@21yangjie.com



